

<u>AN717</u>

Building a 10-bit Bridge Sensing Circuit using the PIC16C6XX and MCP601 Operational Amplifier

Author: Bonnie C. Baker Microchip Technology Inc.

INTRODUCTION

Sensors that use Wheatstone bridge configurations, such as pressure sensors, load cells, or thermistors have a great deal of commonality when it comes to the signal conditioning circuit. This application note delves into the inner workings of the electronics of the signal conditioning path for sensors that use Wheatstone bridge configurations. Analog topics such as gain and filtering circuits will be explored. This discussion is complemented with digital issues such as digital filtering and digital manipulation techniques. Overall, this note's comprehensive investigation of hardware and firmware provides a practical solution including error correction in the data acquisition sensor system.

A sensor that is configured in a Wheatstone bridge typically supplies a low level, differential output signal. The application problem the designer is challenged with is to capture this small signal and eventually convert it to a digital format that gives an 8 to 12 bit representation of the signal.

The inexpensive design strategy shown in the block diagram in Figure 1 uses a low pass filter prior to digitization. The conversion from analog to digital is performed with the microcontroller (MCU). The MCU used in this circuit must have internal analog functions such as a voltage reference and a comparator. These internal analog building blocks are used to implement a first order modulator. This is combined with the MCU's computing power where a digital filter can be implemented.



FIGURE 1: The bridge sensor signal conditioning chain filters high frequency noise in the analog domain then immediately digitizes it with a microcontroller.

BRIDGE SENSOR DATA ACQUISITION CIRCUIT IMPLEMENTATION

Figure 2 gives a detailed circuit for the block diagram shown in Figure 1. The analog portion of this circuit consists of the sensor (in this example a $1.2k\Omega$, 2mV/V load cell), an analog multiplexer, an amplifier and an R/C network. (A complete list of the load cell's specifications is given in Table 1.) An analog multiplexer is used to switch the two sensor outputs between a single ended signal path to the controller. The amplifier is configured as a buffer and used to isolate the sensor load from the R/C network. The R/C network implements the integrator function of a first order modulator. This network can also be used to adjust the input range to the MCU.

Rated Capacity	32 ounces (896 g)
Excitation	$5V_{DC}$ to $12V_{DC}$
Rated Output	2mV/V ±20%
Zero Balance	±0.3mV/V
Operating Temperature	-55 to 95°C
Compensated Temperature	-5 to 50°C
Zero Balance over Tempera- ture	0.036% FS/°C
Output over Temperature	0.036% FS/°C
Resistance	1200Ω ±300Ω
Safe Overload	150%
Full-Scale Deflection	0.01" to 0.05"

TABLE 1: Load Cell, LCL816G (Omega) Specifications.



FIGURE 2: The combination of an R/C network and the microcontroller's analog peripherals can be used to perform an A/D conversion function.

In this circuit, the integrator function of the modulator is implemented with an external capacitor, C_{INT}. When RA3 of the PIC16C6XX is set high, the voltage at RA0 increases in magnitude. This occurs until the output of the comparator (CMCON<6>) is triggered low. At this point, the driver to the RA3 output is switched from high to low. Once this has transpired, the voltage at the input to the comparator (RA0) decreases. This occurs until the comparator is tripped high. At this point, RA3 is set high and the cycle repeats. While the modulator section of this circuit is cycling, two counters are used to keep track of the time and of the number of ones versus zeros that occur at the output of the comparator. The firmware flow chart for this conversion process is shown in Figure 3.



FIGURE 3: This microcontroller A/D conversion flow chart is implemented with the circuit shown in Figure 2. Care should be taken to make the time that every cycle takes through the flow chart constant.

After the timing counter goes to 1024 on one side of the Wheatstone bridge, the MCU switches the multiplexer (A2) to the leg of the other side of the sensor. With the voltage of the other leg of the sensor connected to the input of the amplifier, the controller cycles through another conversion for 1024 counts. The two results from these cycles are subtracted, giving the conversion results. This technique provides 10-bits of resolution with 9.9-bits of accuracy (rms).

The design equations for this circuit are:

$$V_{IN (CM)} = V_{REF3}$$

 $V_{IN (P to P)} = V_{RA3 (P to P)} (R_1 / R_2)$
with $V_{IN (CM)}$ approximates V_{DD} /2 or is equal to
 $(LC_P + LC_N)/2$,

where:

 V_{REF3} is the voltage reference applied to the comparator's non-inverting input and equal to approximately V_{SENSOR} /2. If made external, this reference voltage can be used to adjust offset errors

 $V_{IN (P \text{ to } P)}$ is equal to $(LC_{P(MAX)} - LC_{N(MIN)})$ or $(LC_{P(MIN)} - LC_{N(MAX)})$ which equals the sensor full scale range and $V_{RA3 (P \text{ to } P)}$ is equal to $V_{RA3 (MAX)} - V_{RA3 (MIN)}$ or

approximately V_{DD}

The system in this application note has been designed to have a full-scale input range to the comparator of \pm 40.5mV. Given 9.9-bit (rms) accuracy, the LSB size is 84.7 μ V.

The transfer function of the percentage of ones counted versus input voltage is shown in Figure 4. In this diagram, both the duty cycle between ones and zeros as well as the pulse width is modulated.



FIGURE 4: The relationship between input voltage and the number of ones that are counted by the controller is shown conceptually with this diagram. At low input voltages, the output of the comparator produces very few zeros within the 1024 counts. At voltages in the center of the input range, the comparator quickly toggles between ones and zeros. At higher voltages, the comparator output produces mostly zeros and very few ones.

ERROR SOURCES AND SYSTEM SOLUTIONS

A wheatstone bridge is designed to give a differential output rendering a small voltage that changes proportionally to the sensor's excitation, i.e. pressure or temperature, etc. The dominant types of errors that a sensor exhibits in its transfer function can be categorized as offset, gain, linearity, noise, and thermal. These sensors also produce other errors such as hysteresis, repeatability, stability and aging that are beyond the scope of this application note. An equal contributor to the overall system errors is the offset, gain, and linearity errors from the active components in the signal conditioning path.

OFFSET ERRORS

The offset error of a system can be mathematically described with a constant additive to the entire transfer function as shown in Figure 5.

FIGURE 5: The offset error of a system can be described graphically with a transfer function that has shifted along the *x*-axis.

Typically, offset error is measured at a point where the input signal to the system is zero. This technique provides an output signal that is equal to the offset. This type of error can originate at the sensor or within the various components in the analog signal path. By definition, the offset error is repeatable and stable at a specified operating condition. If the operating conditions change, such as temperature, voltage excitation or current excitation, the offset error may also change.

The offset errors in this signal path come from the wheatstone bridge sensor, the operational amplifier (A1) offset, the port leakage current at RA0, the internal voltage reference (V_{REF3}) offset, the comparator offset, and the non-symmetrical output port of RA3. The only difference in the signal path of the two sensor outputs is the multiplexer channel, which interfaces directly with a high impedance CMOS operational amplifier. Otherwise, both sensor output signals are configured to travel down the same signal-conditioning path. Consequently, the conversion data taken from the positive leg

of the load cell sensor (LC_p) has the same offset and gain errors as the conversion data taken from the negative output of the load cell sensor (LP_N), with the exception of the bridge's offset error.

To accommodate these errors, the design equations for this circuit remains:

 $V_{IN (CM)} = V_{REF3}$

 $V_{IN(P \ to \ P)} = V_{RA3} \left(P \ to \ P\right) \left(R_1 \ / \ R_2\right)$

But, now the worst case variation of $V_{IN(P \ to \ P)}$ is equal to $(LC_{P(MAX)} - LC_{P(MIN)} + LC_{OFF} + A1_{OFF} + RA0_{OFF} + V_{REF3-OFF} + COMP_{OFF} + RA3_{OFF})$

where:

 ΔLC_{OFF} is the maximum offset voltage that can be generated by the load cell bridge

A1_{OFF} is the offset voltage of the operational amplifier

 $RA0_{OFF}$ is the offset error caused by the leakage current of port RA0. This leakage current is specified at 1nA at room temperature and 0.5µA (max) over temperature. This leakage current causes a voltage drop across the parallel combination of R₁ and R₂

 $V_{REF3\text{-}OFF}$ is the offset error of the internal voltage reference of the MCU or $V_{\rm DD}/2$. This error can be reduced significantly with an external voltage reference

 $\textit{COMP}_{\textit{OFF}}$ is the offset of the internal comparator of the MCU and

 $RA3_{OFF}$ is caused by the inability of RA3 to go completely to the rails. It can be quantified by $RA3_{OFF} = ((V_{DD} - RA3_{HIGH}) - RA3_{LOW})/2$. This formula assumes $V_{REF3} = V_{DD}/2$

The maximum magnitudes of these errors are summarized in Table 2.

Error Source	Offset Voltage over Temperature
Load Cell Bridge	±1.5mV in a 5V system
Op Amp	±2mV
Port Leakage, RA0	±1.3mV
Internal V _{REF}	±49mV
Comparator	±10mV
Output Port, RA3 (asymmetrical output swing)	5.5mV

TABLE 2: Maximum offset errors over temperature for the circuit shown in Figure 3.

Firmware Offset Calibration

The offset errors of the circuit can be calibrated in firmware. This is performed by subtracting the conversion code results of the positive leg of the sensor from the results of the negative leg of the sensor. The analog representation of the result of this calculation in firmware is:

$$V_{OUT} = LC_P + LC_{OFF} + A1_{OFF} + RA0_{OFF} + V_{REF3-OFF} + COMP_{OFF} + RA3_{OFF} - LC_N - A1_{OFF} - RA0_{OFF} - V_{REF3-OFF} - COMP_{OFF} - RA3_{OFF}$$
$$V_{OUT} = LC_P - LC_N + LC_{OFF}$$

This result illustrates the efficiency of using firmware to eliminate most of the offset errors, however, the trade-off for having offset adjustments performed by the MCU is dynamic range. In anticipation of these offset errors, the designer should increase the peak-to-peak analog input range of the conversion system. This will result in a conversion that has a wider dynamic range, consequently, lower accuracy.

To counteract this, the accuracy can be improved if more samples are taken in the conversion process. This technique will elongate the overall conversion time. Another technique that can be used is to perform a simple offset adjust in hardware which can be implemented with the digital potentiometer $(A3_A)$.

Hardware Offset Calibration

Given the design equations for this circuit and the errors in Table 2, the total expected offset error over temperature for the electronics is ± 69.3 mV. With a sensor full-scale range of ± 10 mV, the dynamic range of the system would be ~7.9 times larger than the nominal, error free peak-to-peak range at the input of the comparator.

The 8-bit, $1k\Omega$ digital potentiometer (A3_A) in Figure 2 is placed in series between the power supply (5V) with two $10k\Omega$, 1% resistors. This configuration provides a voltage reference range to the comparator of ±119mV centered around mid-supply (2.5V) with a resolution of 0.5mV. If an external reference is used with a ±0.5mV error range, the electronics will contribute ±20.8mV offset error over temperature. This changes the worst case full-scale peak-to-peak range of the system to ±30.8mV. This is only approximately three times larger than the nominal full-scale output (±10mV) of the sensor.

System Span (Gain) Errors

The span or gain of a system can be mathematically described as a constant, which is multiplied against the input signal. The magnitude of the span can easily be determined using the formula below:

Ideal Output = Input x Gain

Span error is the deviation of the span multiple from ideal and can be described with the formula below:

Actual Output = Input x Span (1 + Span Error)

Examples of transfer functions with span error are shown in Figure 6. The plots in Figure 6 do not have offset errors.

FIGURE 6: Span or gain errors can be described graphically as a transfer function that rotates around the intercept of the x and y-axis.

Firmware Span (Gain) Calibration

For this circuit, the span error of the sensor is less influential than the offset errors on the system. Span errors come from the Load Cell ($\pm 20\%$), the resistors ($\pm 1\%$), capacitor ($\pm 10\%$), and the ON resistance of the RA3 port (0.2%). This circuit can rely on firmware calibration with a reduction in the dynamic range of the system. The combination of the sensor error and the capacitor error increases the requirements on the input range to the modulator configuration.

Hardware Span (Gain) Calibration

Span errors can most effectively be removed in the analog domain. For instance, the span error of the sensor can be adjusted with the sensor's excitation voltage. As a trade-off for this adjustment strategy, the common mode voltage of the sensor is changed, creating offset errors with respect to the reference voltage (VREE3) of the comparator. This problem can be alleviated by making the voltage reference ratiometric to the sensor excitation source. Span errors can also be adjusted with either R_1 or R_2 . In the circuit in Figure 2, the other half of the dual, $1k\Omega$ digital potentiometer (A3_B) is configured to perform this function. This type of adjustment does not change the offset error of the system. Finally, span errors can be corrected with changes to the integration capacitor. Of all of the span adjustments, this one is the most awkward to implement.

SYSTEM LINEARITY ERRORS

Linearity error differs from offset or span errors in that it has a unique affect on each individual code of the digitizing system. Linearity errors are defined as the deviation of the transfer function from a straight line. Some engineers define this error using a line that stretches between the end points of the transfer curve while others define it using a line that is calculated using a "best fit" algorithm. In either case, the linearity errors can cause significant errors in translating the sensor input (pressure, temperature, etc.) to digital code.

Linearity errors come in many forms as shown in Figure 7. Sometimes the linearity error of a system can be characterized with a multi-order polynomial, but more typically this error is difficult to predict from system to system, in which case, firmware piecewise linearization methods are usually used.

FIGURE 7: The linearity error of a sensor or system can sometimes be modeled and understood, which allows the designer to use predetermined algorithms in the MCU to minimize their affect. However, typically, these errors are not easily predicted and difficult to calibrate out of the signal path.

Linearity errors in this system originate primarily in the sensor and secondarily in the remainder of the signal conditioning circuit.

Firmware Linearization

Linearity errors can be calibrated out of the system in firmware using polynomial calculations if the transfer function is understood or piecewise linearization methods if the transfer function from part to part varies. If piecewise linearization is used, calibration data should be taken from the system and stored in EEPROM. Utilizing the calibration data, piecewise linearization is easily implemented using two 16 bit unsigned subtractions, one 16 bit unsigned multiplication and one 16 bit unsigned divide.

 $X_{CAL} = X_{FULL} / (Y_{FULL} - Y_{OFF}) \times (Y_{SAMP} - Y_{ZERO})$ where:

 X_{CAL} is equal to the calibrated results

 $X_{\ensuremath{\textit{FULL}}}$ is the ideal full scale response saved in $\ensuremath{\textit{EEPROM}}$

 Y_{FULL} is the measured full scale response saved in EEPROM

 Y_{OFF} is the measured offset error saved in EEPROM

 Y_{SAMP} is the measured sample that requires linearization and calibration

This style of linearization correction also removes offset and span errors from the digital results.

Hardware Linearization

There are two components that generate linearity errors. The sensor can contribute up to $\pm 0.25\%$ FS error. The capacitor in this circuit can also contribute an appreciable error if care is not taken in limiting the charge and discharge range of the device. If the R/C time constant of the circuit is greater than the inverse of the sample frequency, the non-linearity of this time response will cause a linearity error in the system.

In this case the R/C time constant is equal to:

$$t_{RC} = R_1 ||R_2 \times C_{INT}$$

$$t_{RC} = 2.67 k\Omega ||165 k\Omega \times 1 \mu F$$

$$t_{RC} = 2.627 msec$$

also,
$$t_{RC} <= t_{SAMPLE} / 6.5$$

The maximum voltage deviation due to the non-linearity of the R/C network is ~10mV. This is below a 0.2% error. If a lower sampling frequency is used, the integrating capacitor must be increased in value.

SYSTEM NOISE ERRORS

Noise can plague the best of circuits, particularly circuits that have large analog segments. An effective way to approach noise problems is to use a basic list of guidelines in conjunction with a working knowledge of noise fundamentals. The checklist that every designer should have on hand includes:

- 1. Are bypass capacitors included in the design?
- 2. Is a low impedance ground plane implemented to minimize any ground noise across sensitive analog parts?
- 3. Are appropriate anti-aliasing filters used in front of the A/D converter?
- 4. Are the devices in the circuit too noisy?

Firmware Noise Reduction

The A/D converter described in this application note was modeled after a classic first order delta-sigma topology. In the digital domain, the data collection algorithm implements a simple average engine by default. This style of averaging, otherwise known as digital filtering, is also called a single order sinc filter or Finite Impulse Response (FIR) filter.

Further noise reduction algorithms can be implemented with the PIC MCU which will produce a system with higher accuracy. As an example, a third order FIR filter can be implemented with the following calculations in code:

$$y(n) = (2x(n) + x(n-1) + x(n-2) + x(n-3) + x(n-4) + x(n-5) + x(n-6)) / 8$$

where:

n identifies the measurement sample

y(n) is the output digital results

x(n) is the measurement sample results

This filter is also known as a sinc³ filter.

Other filter types, such as the Infinite Impulse Response (IIR) filter or a decimation filter can also be used to improve accuracy. A detailed discussion of these filters are beyond the scope of this application note, however, references have been provided for further reading.

Hardware Noise Reduction

In Figure 2, the R/C network that is used to implement the integrator function also serves as a low pass filter. This low pass filter is equal to:

$$f_{3dB} = 1 / (2 \pi R_1 || R_2 x C_{INT})$$

Further noise reduction can be implement by adding a second modulator stage at the input so this system. This implementation is shown in Figure 8.

FIGURE 8: An additional modulator stages can reduce noise in the system even further. In this circuit, one modulator stage is added which improves the system from a 9.9-bit accurate (rms) system to an 11.1-bit accurate system.

REFERENCES

Peter, Baker, Butler, Darmawaskita, "Making a Delta-Sigma Converter Using A Microcontroller's Analog Comparator Module", *AN700, Microchip Technology, Inc.*

Baker, Bonnie C., "Anti-aliasing, Analog Filters for Data Acquisition Systems", *AN699, Microchip Technology, Inc.*

Baker, Bonnie C., "Layout Tips for 12-Bit Converter Applications", *AN688, Microchip Technology, Inc.*

Morrison, Ralph, "Noise and Other Interfering Signals", John Wiley & Sons, Inc., 1192

Baker, Bonnie C., "Analog Circuit Noise Sources and Remedies", *EDTN Internet Magazine, Analog Avenue Tech Notes, Oct. 1998*

Baker, Bonnie C., "Noise Sources in Applications Using Capacitive Coupled Isolated Products", *AB-047, Burr-Brown Corp.*

Palacheria, Amar, "Implementing IIR Digital Filters", *AN540, Microchip Technology, Inc.*

Norsworthy, Schreier, Temes, "Delta-Sigma A/D Converters: Theory, Design, and Simulation", *IEEE Press*

WORLDWIDE SALES AND SERVICE

AMERICAS

Corporate Office Microchip Technology Inc. 2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-786-7200 Fax: 480-786-7277 Technical Support: 480-786-7627 Web Address: http://www.microchip.com

Atlanta

Microchip Technology Inc. 500 Sugar Mill Road, Suite 200B Atlanta, GA 30350 Tel: 770-640-0034 Fax: 770-640-0307

Boston

Microchip Technology Inc. 5 Mount Royal Avenue Marlborough, MA 01752 Tel: 508-480-9990 Fax: 508-480-8575

Chicago

Microchip Technology Inc. 333 Pierce Road, Suite 180 Itasca, IL 60143 Tel: 630-285-0071 Fax: 630-285-0075

Dallas

Microchip Technology Inc. 4570 Westgrove Drive, Suite 160 Addison, TX 75248 Tel: 972-818-7423 Fax: 972-818-2924

Dayton

Microchip Technology Inc. Two Prestige Place, Suite 150 Miamisburg, OH 45342 Tel: 937-291-1654 Fax: 937-291-9175

Detroit

Microchip Technology Inc. Tri-Atria Office Building 32255 Northwestern Highway, Suite 190 Farmington Hills, MI 48334 Tel: 248-538-2250 Fax: 248-538-2260

Los Angeles

Microchip Technology Inc. 18201 Von Karman, Suite 1090 Irvine, CA 92612 Tel: 949-263-1888 Fax: 949-263-1338

New York

Microchip Technology Inc. 150 Motor Parkway, Suite 202 Hauppauge, NY 11788 Tel: 631-273-5305 Fax: 631-273-5335

San Jose

Microchip Technology Inc. 2107 North First Street, Suite 590 San Jose, CA 95131 Tel: 408-436-7950 Fax: 408-436-7955

AMERICAS (continued)

Toronto

Microchip Technology Inc. 5925 Airport Road, Suite 200 Mississauga, Ontario L4V 1W1, Canada Tel: 905-405-6279 Fax: 905-405-6253 ASIA/PACIFIC

Hong Kong Microchip Asia Pacific Unit 2101, Tower 2 Metroplaza 223 Hing Fong Road Kwai Fong, N.T., Hong Kong Tel: 852-2-401-1200 Fax: 852-2-401-3431 Beijing Microchip Technology, Beijing Unit 915, 6 Chaoyangmen Bei Dajie Dong Erhuan Road, Dongcheng District New China Hong Kong Manhattan Building Beijing 100027 PRC Tel: 86-10-85282100 Fax: 86-10-85282104 India Microchip Technology Inc. India Liaison Office No. 6, Legacy, Convent Road Bangalore 560 025, India Tel: 91-80-229-0061 Fax: 91-80-229-0062 Japan

Microchip Technology Intl. Inc. Benex S-1 6F 3-18-20, Shinyokohama Kohoku-Ku, Yokohama-shi Kanagawa 222-0033 Japan Tel: 81-45-471- 6166 Fax: 81-45-471-6122 Korea Microchip Technology Korea

168-1, Youngbo Bldg. 3 Floor Samsung-Dong, Kangnam-Ku Seoul, Korea Tel: 82-2-554-7200 Fax: 82-2-558-5934 Shanghai

Microchip Technology RM 406 Shanghai Golden Bridge Bldg. 2077 Yan'an Road West, Hong Qiao District Shanghai, PRC 200335 Tel: 86-21-6275-5700 Fax: 86 21-6275-5060

ASIA/PACIFIC (continued)

Singapore Microchip Technology Singapore Pte Ltd. 200 Middle Road #07-02 Prime Centre Singapore 188980 Tel: 65-334-8870 Fax: 65-334-8850

Taiwan, R.O.C

Microchip Technology Taiwan 10F-1C 207 Tung Hua North Road Taipei, Taiwan, ROC

Tel: 886-2-2717-7175 Fax: 886-2-2545-0139 **EUROPE**

United Kingdom

Arizona Microchip Technology Ltd. 505 Eskdale Road Winnersh Triangle Wokingham Berkshire, England RG41 5TU Tel: 44 118 921 5858 Fax: 44-118 921-5835

Denmark

Microchip Technology Denmark ApS **Regus Business Centre** Lautrup hoj 1-3 Ballerup DK-2750 Denmark Tel: 45 4420 9895 Fax: 45 4420 9910

France

Arizona Microchip Technology SARL Parc d'Activite du Moulin de Massy 43 Rue du Saule Trapu Batiment A - ler Etage 91300 Massy, France Tel: 33-1-69-53-63-20 Fax: 33-1-69-30-90-79

Germany

Arizona Microchip Technology GmbH Gustav-Heinemann-Ring 125 D-81739 München, Germany Tel: 49-89-627-144 0 Fax: 49-89-627-144-44 Italy

Arizona Microchip Technology SRL Centro Direzionale Colleoni Palazzo Taurus 1 V. Le Colleoni 1 20041 Agrate Brianza Milan, Italy Tel: 39-039-65791-1 Fax: 39-039-6899883

11/15/99

DNV MSC **DNV Certification. Inc** USA The Netherland Accredited by the RvA ANSI * RAB CCRED DIN ISO 9001 / QS-9000 **REGISTERED FIRM**

Microchip received QS-9000 quality system certification for its worldwide headquarters, design and wafer fabrication facilities in Chandler and Tempe, Arizona in July 1999. The Company's quality system processes and procedures are QS-9000 compliant for its PICmicro[®] 8-bit MCUs, KEELOQ[®] code hopping devices, Serial EEPROMs and microperipheral products. In addition, Microchip's quality system for the design and manufacture of development systems is ISO 9001 certified.

Printed on recycled paper. All rights reserved. © 1999 Microchip Technology Incorporated. Printed in the USA. 11/99

Information contained in this publication regarding device applications and the like is intended for suggestion only and may be superseded by updates. No representation or warranty is given and no liability is assumed by Microchip Technology Incorporated with respect to the accuracy or use of such information, or infiningement of patents or other intellectual property rights arising from such use or otherwise. Use of Microchip's products as critical components in life support systems is not authorized except with express written approval by Microchip. No incorpose and no version of the other support systems is not authorized except with express written approval by Microchip. No incorpose are registered trademarks of Microchip Technology Inc. in the U.S.A. and other countries. All rights reserved. All other trademarks mentioned herein are the property of their respective companies.

